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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Applicant:

Chris E. Barns et al.

Serial No.: 10/629,127

Filed: July 29, 2003

For: Preventing Silicide Formation at  
the Gate Electrode in a Replacement  
Metal Gate Technology

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Art Unit: 2822

Examiner: Khanh B. Duong

Docket: ITL.1016US  
P16703

Assignee: Intel Corporation

*Fee Sheet*

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**REPLY TO PAPER NO. 20050207**

Sir:

In response to the office action mailed March 8, 2005, please amend the above-referenced patent application as follows:

05/26/2005 ADAVID 00000001 201504 10629127

01 FC:1202 150.00 DA

Date of Deposit: May 17, 2005

I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

*Cynthia L. Hayden*  
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